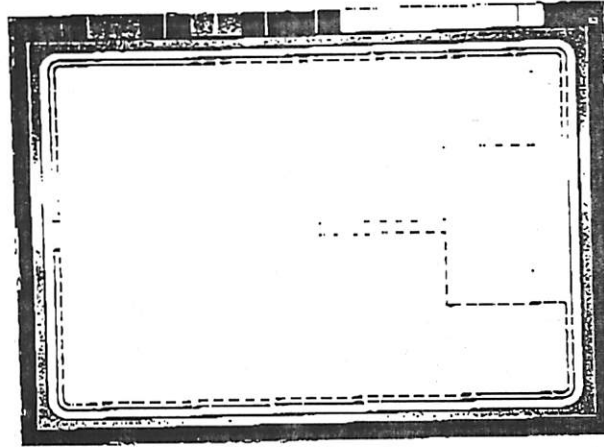


DEVICE	CATEGORY	MANUFACTURER	REV.NO.	
BUZ71/71A	MOSFET	SILICONIX	MASK NO.	

STANDARD PACKAGE:

Die Topology: N

SOURCE



GATE

BACKSIDE : DRAIN

Note: STD BACKSIDE METAL IS TITANIUM-NICKEL-SILVER

SIZE: _____ m.m.
92 x 72 mils.

PIN/PAD FUNCTION:

1.	9.	17.	25.
2.	10.	18.	26.
3.	11.	19.	27.
4.	12.	20.	28.
5.	13.	21.	29.
6.	14.	22.	30.
7.	15.	23.	31.
8.	16.	24.	32.

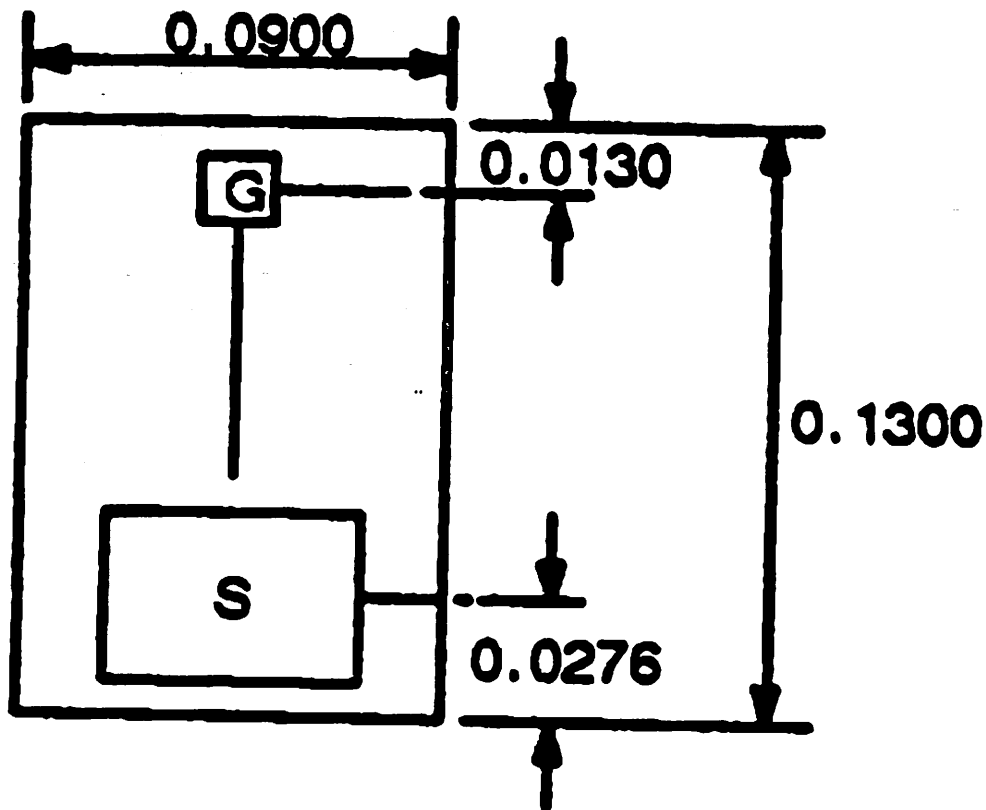


NELSON ROAD INDUSTRIAL ESTATE
DARTMOUTH, DEVON, TQ6 9LA,
UNITED KINGDOM.

TITLE: BUZ71/71A
N CHANNEL ENHANCEMENT MODE MOSFET

ISSUE	AUTHORISED:	DATE:
A	<i>P. J. [Signature]</i>	25.7.92.

RECEIVED



Gate Pad: 0.0183 X 0.0142
Source Pad: 0.0528 X 0.0394

TOPOLOGY T

Real:199 Geometry for both BUZ71, and BUZ171

QUOTE# 990152

Jean Pierre